



## Ultrafast Rectifier

MUR1020CT  
MURB1020CT  
MURB1020CT-1

### Features

- Ultrafast Recovery Time
- Low Forward Voltage Drop
- Low Leakage Current
- 175°C Operating Junction Temperature

$t_{rr} = 25\text{ns}$   
 $I_{F(AV)} = 10\text{Amp}$   
 $V_R = 200\text{V}$

### Description/Applications

International Rectifier's MUR.. series are the state of the art Ultra fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultra fast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC-DC converters as well as free-wheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

### Absolute Maximum Ratings

Parameters		Max	Units
$V_{RRM}$	Peak Repetitive Peak Reverse Voltage	200	V
$I_{F(AV)}$	Average Rectified Forward Current Per Leg	5	A
	Total Device, (Rated $V_R$ ), $T_C = 149^\circ\text{C}$ Total Device	10	
$I_{FSM}$	Non Repetitive Peak Surge Current Per Leg	50	
$I_{FM}$	Peak Repetitive Forward Current Per Leg	10	
(Rated $V_R$ , Square wave, 20 KHz), $T_C = 149^\circ\text{C}$			
$T_J, T_{STG}$	Operating Junction and Storage Temperatures	- 65 to 175	$^\circ\text{C}$

Case Styles		
MUR1020CT	MURB1020CT	MURB1020CT-1
TO-220AB	D2PAK	TO-262

MUR1020CT, MURB1020CT, MURB1020CT-1

Bulletin PD-20738 rev. A 01/01

International  
**IR** Rectifier

### Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameters		Min	Typ	Max	Units	Test Conditions
$V_{BR}$ , $V_r$	Breakdown Voltage, Blocking Voltage	200	-	-	V	$I_R = 100\mu\text{A}$
$V_F$	Forward Voltage	-	0.87	0.99	V	$I_F = 5\text{A}, T_J = 125^\circ\text{C}$
		-	1.02	1.20	V	$I_F = 10\text{A}, T_J = 125^\circ\text{C}$
		-	1.12	1.25	V	$I_F = 10\text{A}, T_J = 25^\circ\text{C}$
$I_R$	Reverse Leakage Current	-	-	10	$\mu\text{A}$	$V_R = V_R$ Rated
		-	-	250	$\mu\text{A}$	$T_J = 150^\circ\text{C}, V_R = V_R$ Rated
$C_T$	Junction Capacitance	-	8	-	pF	$V_R = 200\text{V}$
$L_S$	Series Inductance	-	8.0	-	nH	Measured lead to lead 5mm from package body

### Dynamic Recovery Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameters		Min	Typ	Max	Units	Test Conditions
$t_{rr}$	Reverse Recovery Time	-	-	35	ns	$I_F = 1.0\text{A}, dI_F/dt = 50\text{A}/\mu\text{s}, V_R = 30\text{V}$
		-	-	25		$I_F = 0.5\text{A}, I_R = 1.0\text{A}, I_{REC} = 0.25\text{A}$
		-	24	-		$T_J = 25^\circ\text{C}$
		-	35	-		$T_J = 125^\circ\text{C}$
$I_{RRM}$	Peak Recovery Current	-	3.3	-	A	$T_J = 25^\circ\text{C}$
		-	5.0	-		$T_J = 125^\circ\text{C}$
$Q_{rr}$	Reverse Recovery Charge	-	33	-	nC	$T_J = 25^\circ\text{C}$
		-	76	-		$T_J = 125^\circ\text{C}$

### Thermal - Mechanical Characteristics

Parameters			Min	Typ	Max	Units		
$T_J$	Max. Junction Temperature Range		-	-	-65 to 175	°C		
$T_{Stg}$	Max. Storage Temperature Range		-	-	-65 to 175			
$R_{thJC}$	Thermal Resistance, Junction to Case	Per Leg	-	-	5	°C/W		
$R_{thJA}$ <sup>①</sup>	Thermal Resistance, Junction to Ambient	Per Leg	-	-	50			
$R_{thCS}$ <sup>②</sup>	Thermal Resistance, Case to Heatsink		-	0.5	-			
$W_t$	Weight		-	2.0	-	g		
			-	0.07	-	(oz)		
Mounting Torque			6.0	-	12	Kg-cm		
			5.0	-	10	lbf.in		

① Typical Socket Mount

② Mounting Surface, Flat, Smooth and Greased

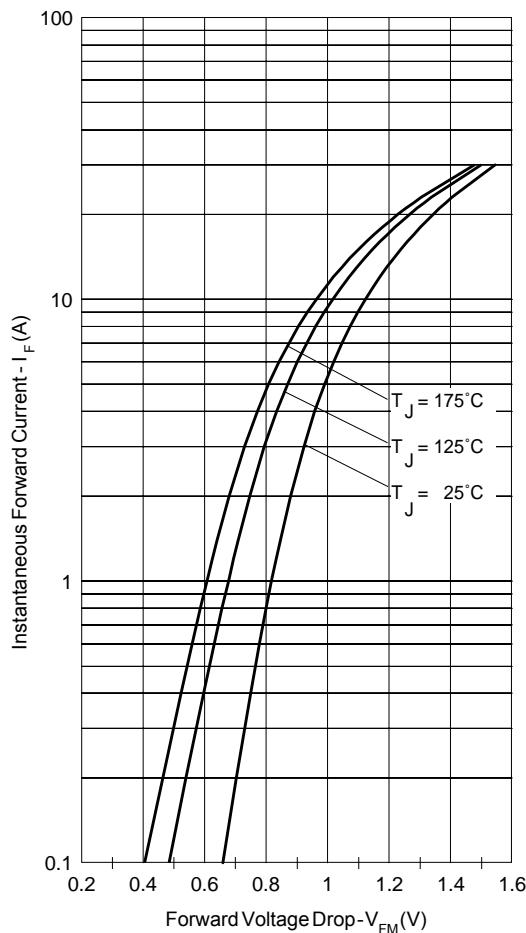


Fig. 1-Typical Forward Voltage Drop Characteristics

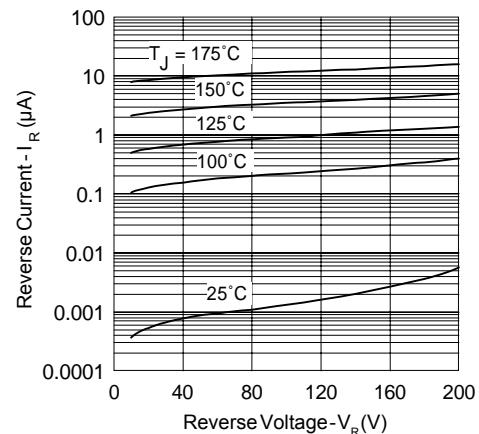


Fig. 2-Typical Values Of Reverse Current Vs. Reverse Voltage

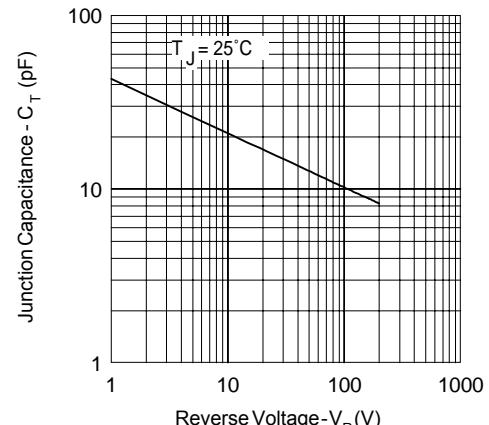


Fig. 3-Typical Junction Capacitance Vs. Reverse Voltage

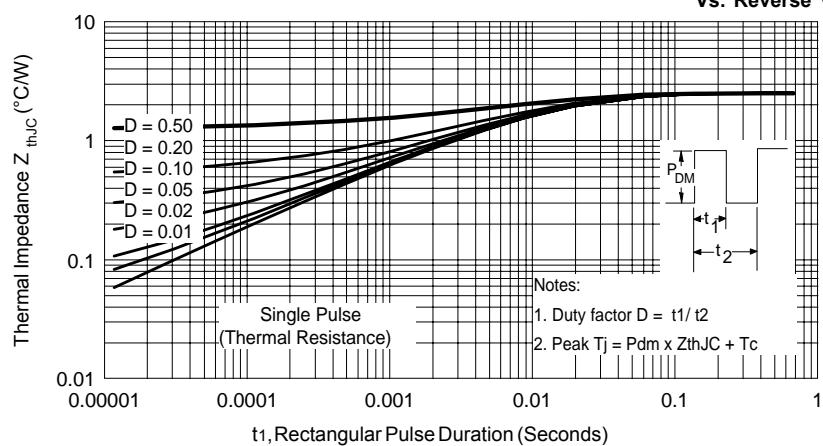
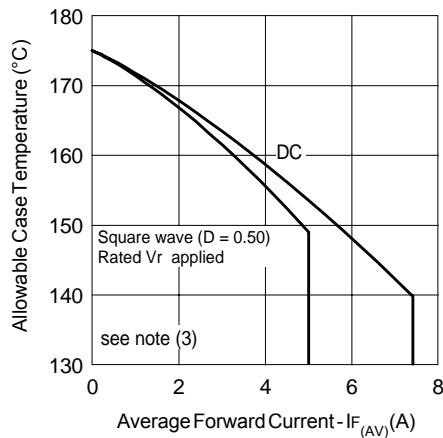
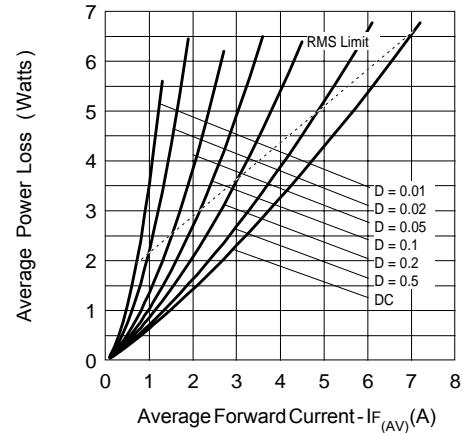


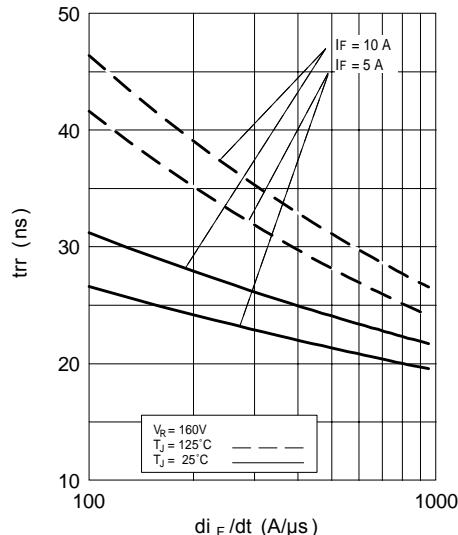
Fig. 4-Max. Thermal Impedance  $Z_{thJC}$  Characteristics



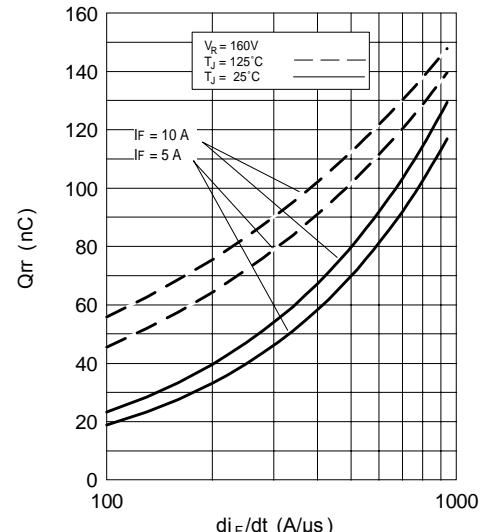
**Fig. 5 - Max. Allowable Case Temperature Vs. Average Forward Current**



**Fig. 6 - Forward Power Loss Characteristics**



**Fig. 7 - Typical Reverse Recovery vs. di<sub>F</sub>/dt**



**Fig. 8 - Typical Stored Charge vs. di<sub>F</sub>/dt**

(3) Formula used:  $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$ ;  
 $P_d = \text{Forward Power Loss} = I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$  (see Fig. 6);  
 $P_{d_{REV}} = \text{Inverse Power Loss} = V_{R1} \times I_R (1 - D)$ ;  $I_R @ V_{R1} = \text{rated } V_R$

### Reverse Recovery Circuit

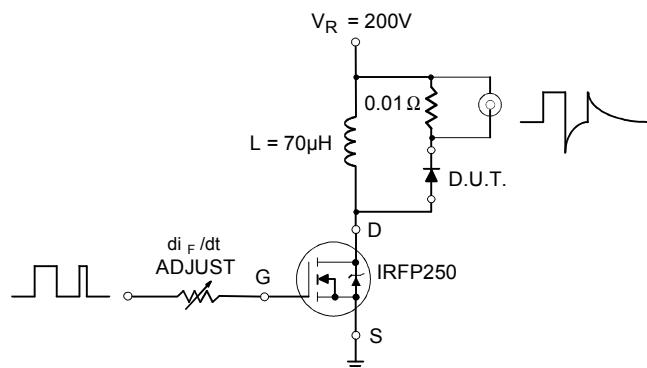
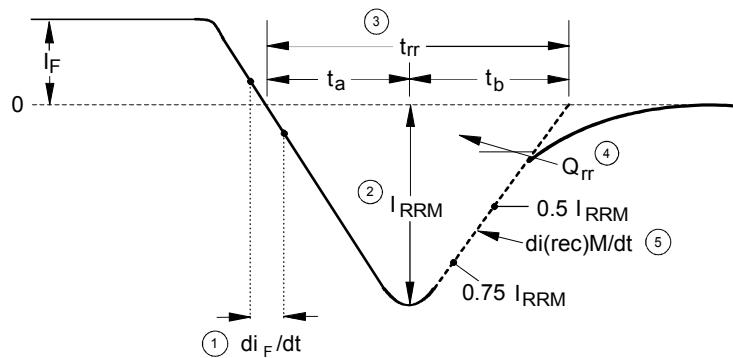


Fig. 9- Reverse Recovery Parameter Test Circuit



1.  $di_F/dt$  - Rate of change of current through zero crossing

2.  $I_{RRM}$  - Peak reverse recovery current

3.  $t_{rr}$  - Reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.50 I_{RRM}$  extrapolated to zero current

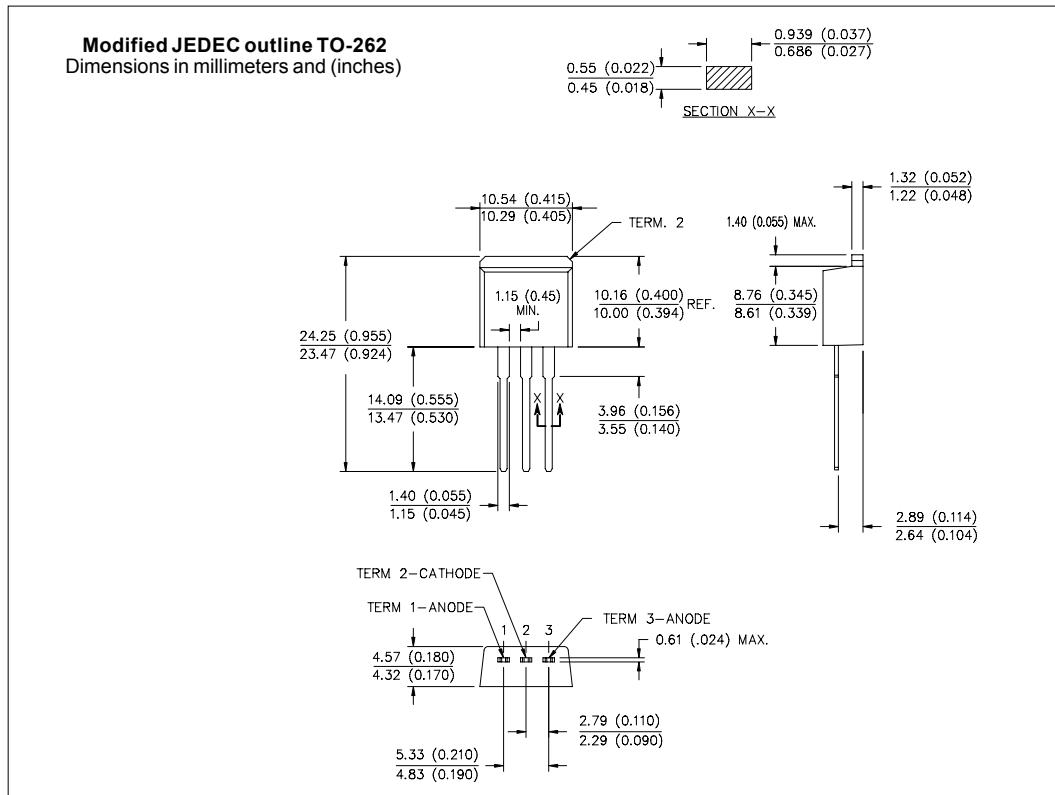
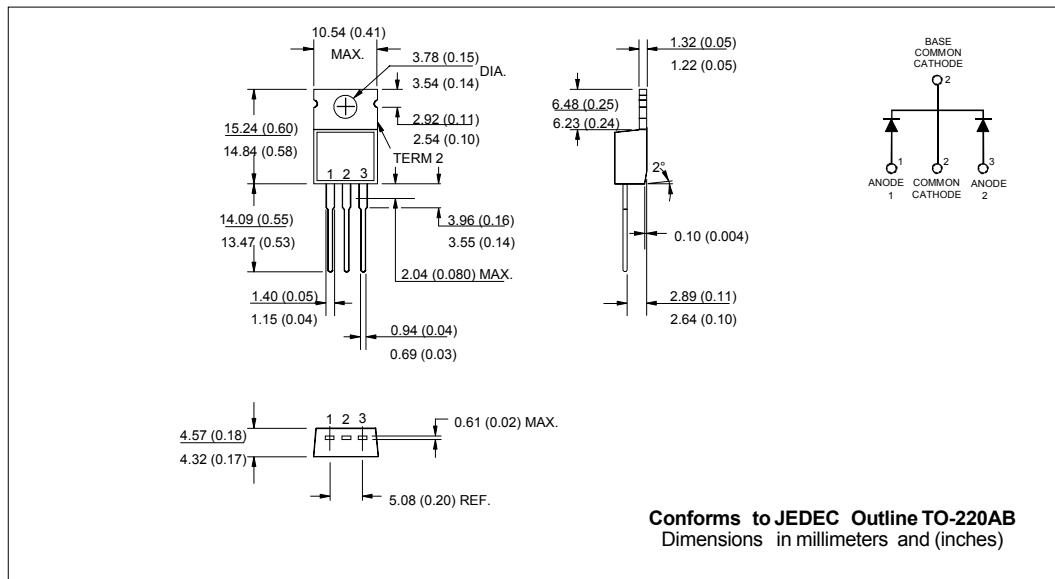
4.  $Q_{rr}$  - Area under curve defined by  $t_{rr}$  and  $I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

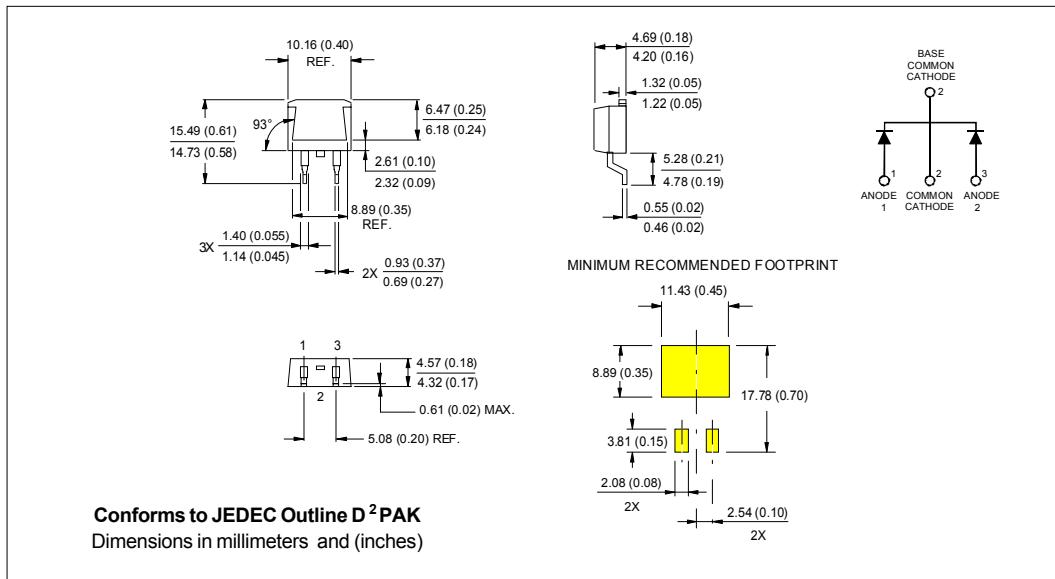
5.  $di(\text{rec})M/dt$  - Peak rate of change of current during  $t_b$  portion of  $t_{rr}$

Fig. 10 - Reverse Recovery Waveform and Definitions

### Outline Table



## Outline Table



## Ordering Information Table

Device Code					
<b>MUR</b>	<b>B</b>	<b>10</b>	<b>20</b>	<b>CT</b>	<b>-1</b>
(1)	(2)	(3)	(4)	(5)	(6)
<b>1</b>	- Ultrafast MUR Series				
<b>2</b>	- B = D <sup>2</sup> Pak / TO-262				
	None = TO-220AB				
<b>3</b>	- Current Rating (10 = 10A)				
<b>4</b>	- Voltage Rating (20 = 200V)				
<b>5</b>	- CT = Center Tap(Dual)TO-220/D <sup>2</sup> PAK/TO-262				
<b>6</b>	- "-1" = TO-262 Option				

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**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7309  
Visit us at [www.irf.com](http://www.irf.com) for sales contact information. 01/01